

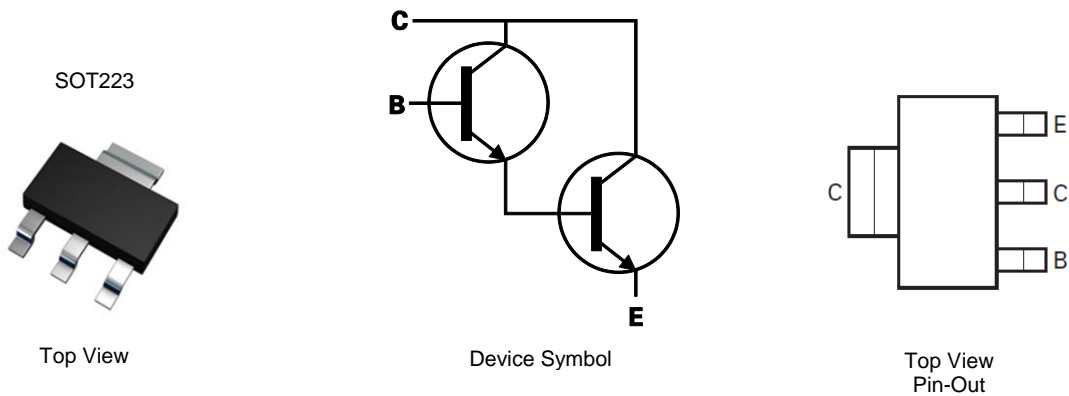
**80V NPN DARLINGTON TRANSISTOR IN SOT223**

**Features**

- $BV_{CEO} > 80V$
- $BV_{CBO} > 100V$
- $I_C = 2A$  High Continuous Current
- Useful hFE up to 6A
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.112 grams (Approximate)

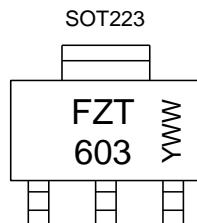


**Ordering Information** (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT603TA	FZT603	7	12	1,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



FZT 603 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Last Digit of Year (ex: 5= 2015)  
 WW or  $\bar{W}W$  = Week Code (01-53)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	100	V
Collector-Emitter Voltage	V <sub>CEO</sub>	80	V
Emitter-Base Voltage	V <sub>EBO</sub>	10	V
Continuous Collector Current	I <sub>C</sub>	2	A
Peak Pulse Current	I <sub>CM</sub>	6	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

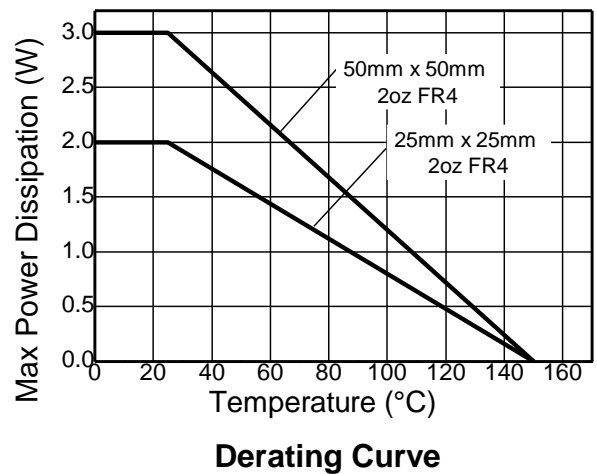
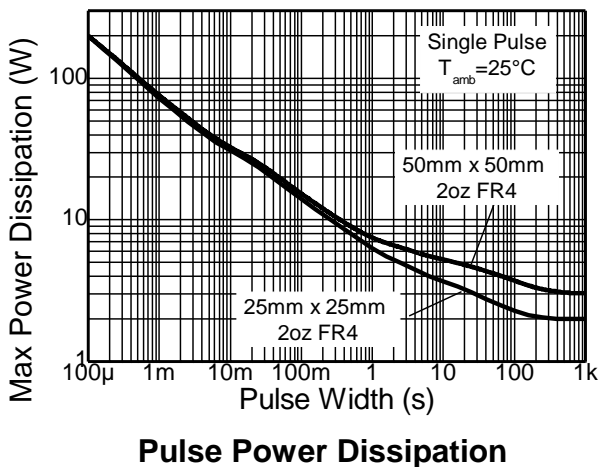
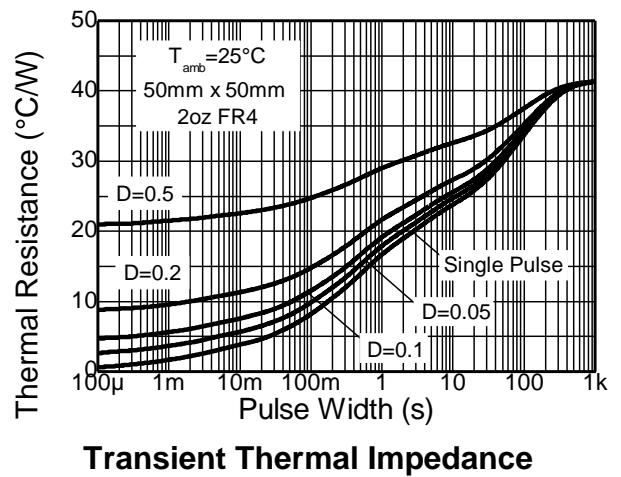
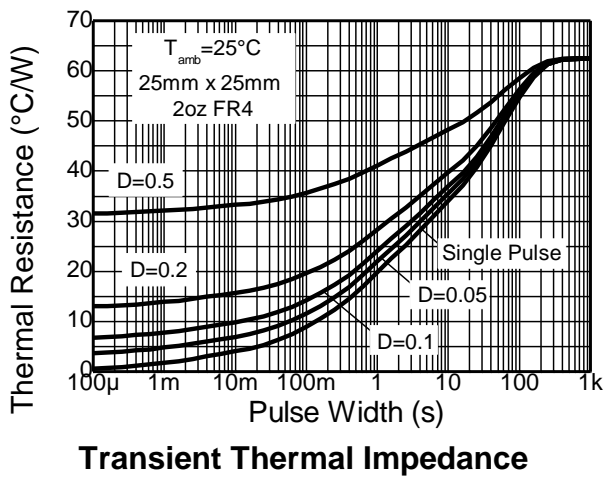
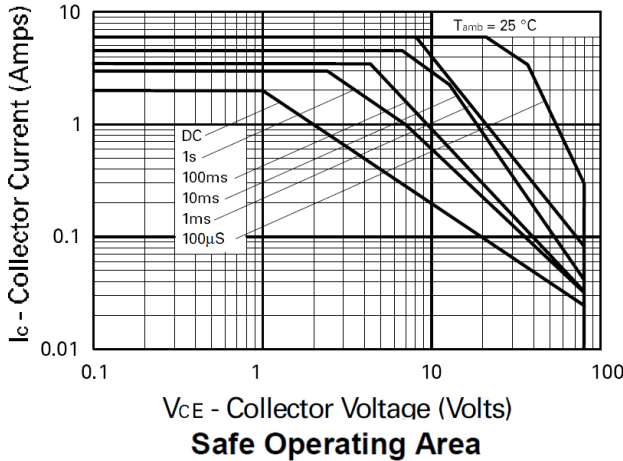
Characteristic	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	(Note 5)	3.0
		(Note 6)	2.0
		(Note 7)	1.6
		(Note 8)	1.2
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	(Note 5)	41.7
		(Note 6)	62.5
		(Note 7)	78.1
		(Note 8)	104
Thermal Resistance Junction to Lead	R <sub>θJL</sub>	12.9	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	2,000	V	2
Electrostatic Discharge - Machine Model	ESD MM	200	V	B

- Notes:
5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
  7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
  8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
  9. Thermal resistance from junction to solder-point (at the end of the collector lead).
  10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Thermal Characteristics and Derating Information**

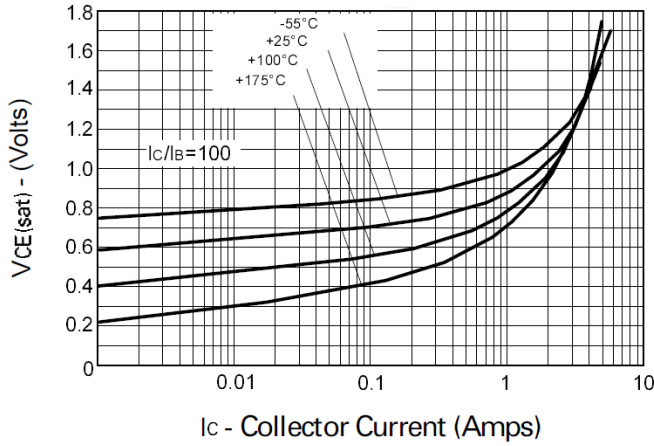


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

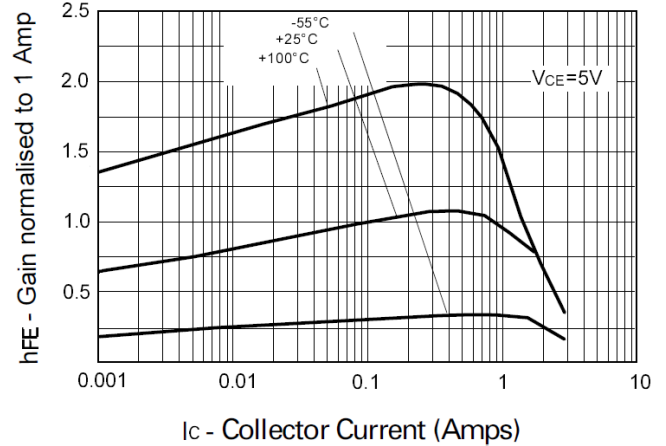
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CB0</sub>	100	240	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	80	110	—	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	10	16	—	V	I <sub>E</sub> = 100μA
Collector-Base Cut-Off Current	I <sub>CB0</sub>	-	—	10	nA	V <sub>CB</sub> = 80V
		-	—	10	μA	V <sub>CB</sub> = 80V, T <sub>A</sub> = +100°C
Collector-Emitter Cut-Off Current	I <sub>CES</sub>	-	—	10	μA	V <sub>CE</sub> = 80V
Emitter Cutoff Current	I <sub>EBO</sub>	-	—	100	nA	V <sub>EB</sub> = 8V
DC Current Gain (Note 11)	h <sub>FE</sub>	3,000 5,000 3,000 2,000	14,000 15,000 14,000 10,000 2,000 750	— 100,000 — — — —	—	I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5V I <sub>C</sub> = 500mA, V <sub>CE</sub> = 5V I <sub>C</sub> = 1A, V <sub>CE</sub> = 5V I <sub>C</sub> = 2A, V <sub>CE</sub> = 5V I <sub>C</sub> = 5A, V <sub>CE</sub> = 5V I <sub>C</sub> = 6A, V <sub>CE</sub> = 5V
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	— —	0.79 0.80 0.88 0.99 0.86	0.88 0.90 1.00 1.13 —	V	I <sub>C</sub> = 250mA, I <sub>B</sub> = 0.25mA I <sub>C</sub> = 0.4A, I <sub>B</sub> = 0.4mA I <sub>C</sub> = 1A, I <sub>B</sub> = 1mA I <sub>C</sub> = 2A, I <sub>B</sub> = 20mA I <sub>C</sub> = 2A, I <sub>B</sub> = 20mA, T <sub>J</sub> = +150°C
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	—	1.70	1.95	V	I <sub>C</sub> = 2A, I <sub>B</sub> = 20mA
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	—	1.50	1.75	V	I <sub>C</sub> = 2A, V <sub>CE</sub> = 5V
Input Capacitance (Note 11)	C <sub>ibo</sub>	—	90	—	pF	V <sub>EB</sub> = 0.5V, f = 1MHz
Output Capacitance (Note 11)	C <sub>obo</sub>	—	15	—	pF	V <sub>CB</sub> = 10V, f = 1MHz
Current Gain-Bandwidth Product (Note 11)	f <sub>T</sub>	150	—	—	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA, f=20MHz
Turn-On Time	t <sub>on</sub>	—	0.5	—	μs	V <sub>CC</sub> = 10V, I <sub>C</sub> = 500mA
Turn-Off Time	t <sub>off</sub>	—	1.6	—	μs	I <sub>B1</sub> = -I <sub>B2</sub> = 0.5mA

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%.

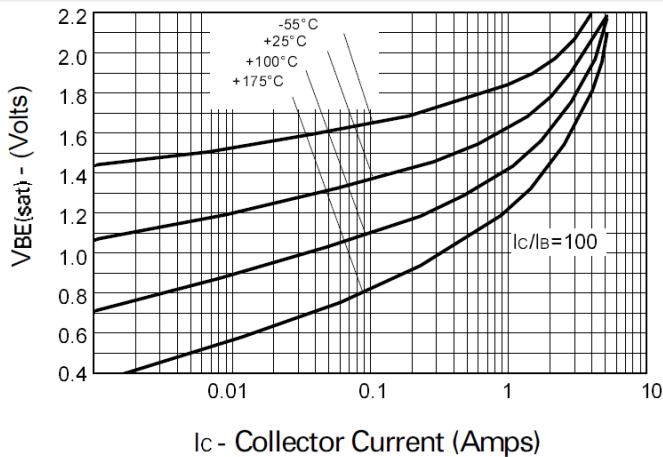
**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)



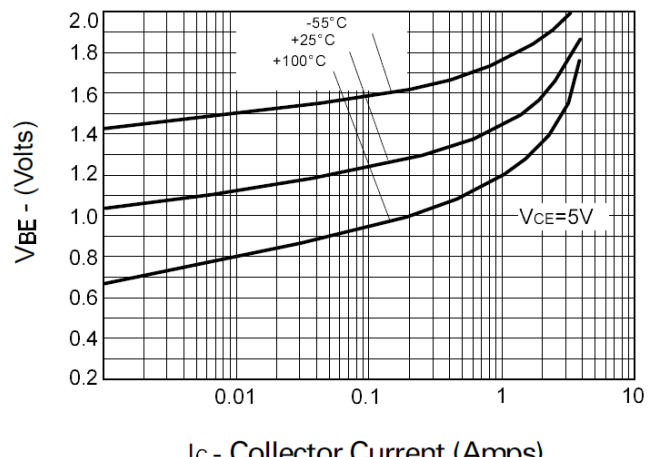
**$V_{CE(sat)}$  v  $I_C$**



**$h_{FE}$  v  $I_C$**



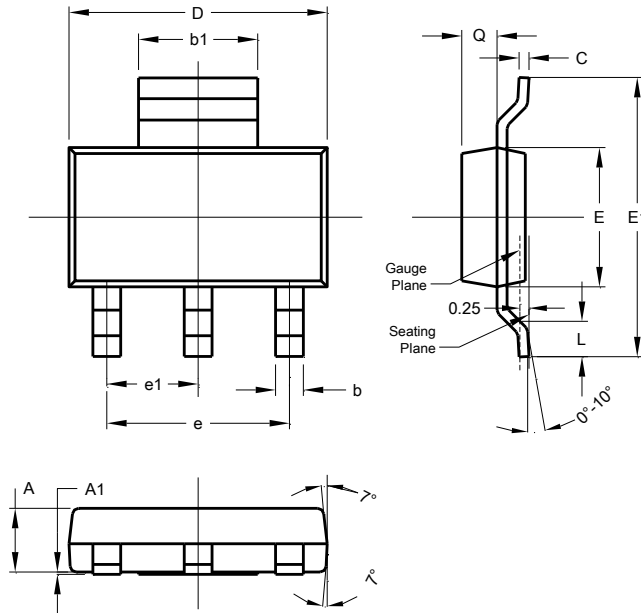
**$V_{BE(sat)}$  v  $I_C$**



**$V_{BE(on)}$  v  $I_C$**

## Package Outline Dimensions

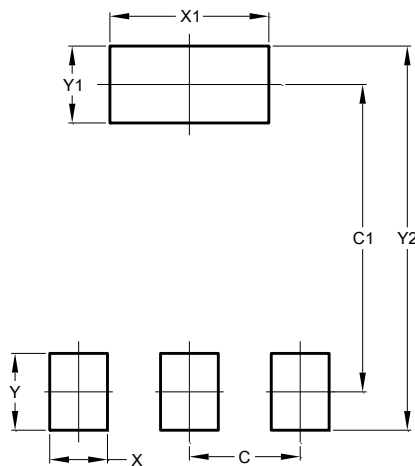
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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